

Silicon NPN Power Transistors

2SD2293

DESCRIPTION

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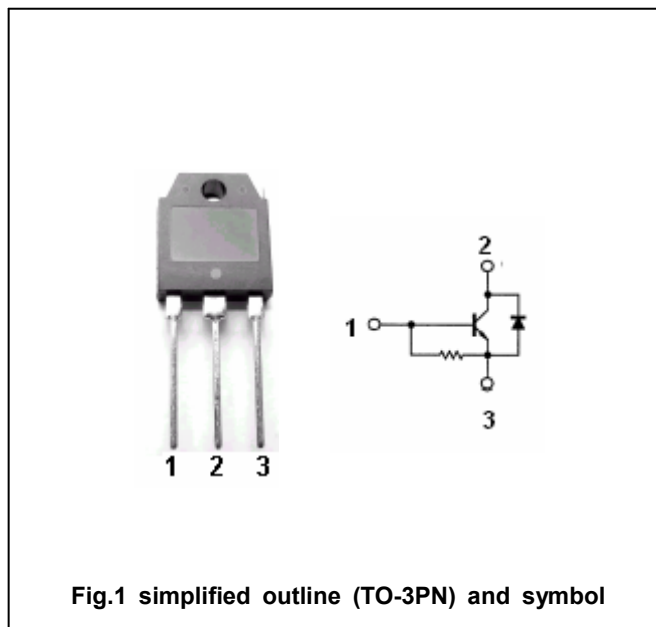
- With TO-3PN package
- High voltage
- Built-in damper diode

APPLICATIONS

- For color TV horizontal deflection output applications

PINNING

PIN	DESCRIPTION
1	Base
2	Collector;connected to mounting base
3	Emitter

Absolute maximum ratings ($T_a=25^\circ\text{C}$)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	1500	V
V_{CEO}	Collector-emitter voltage	Open base	700	V
V_{EBO}	Emitter-base voltage	Open collector	6	V
I_C	Collector current		3	A
P_C	Collector power dissipation	$T_C=25^\circ\text{C}$	50	W
T_j	Junction temperature		150	$^\circ\text{C}$
T_{stg}	Storage temperature		-55-150	$^\circ\text{C}$

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CHARACTERISTICS

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 $T_j = 25^\circ\text{C}$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{CEO(SUS)}$	Collector-emitter sustaining voltage	$I_C = 100\text{mA}$; $I_B = 0$	700			V
$V_{EBO(BR)}$	Emitter-base breakdown voltage	$I_E = 350\text{mA}$; $I_C = 0$	6			V
V_{CEsat}	Collector-emitter saturation voltage	$I_C = 2.5\text{A}$; $I_B = 0.8\text{A}$			5.0	V
V_{BEsat}	Base-emitter saturation voltage	$I_C = 2.5\text{A}$; $I_B = 0.8\text{A}$			1.5	V
h_{FE}	DC current gain	$I_C = 0.5\text{A}$; $V_{CE} = 5\text{V}$	8			
I_{CES}	Collector cut-off current	$V_{CE} = 1500\text{V}$; $V_{BE} = 0$			0.5	mA

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PACKAGE OUTLINE

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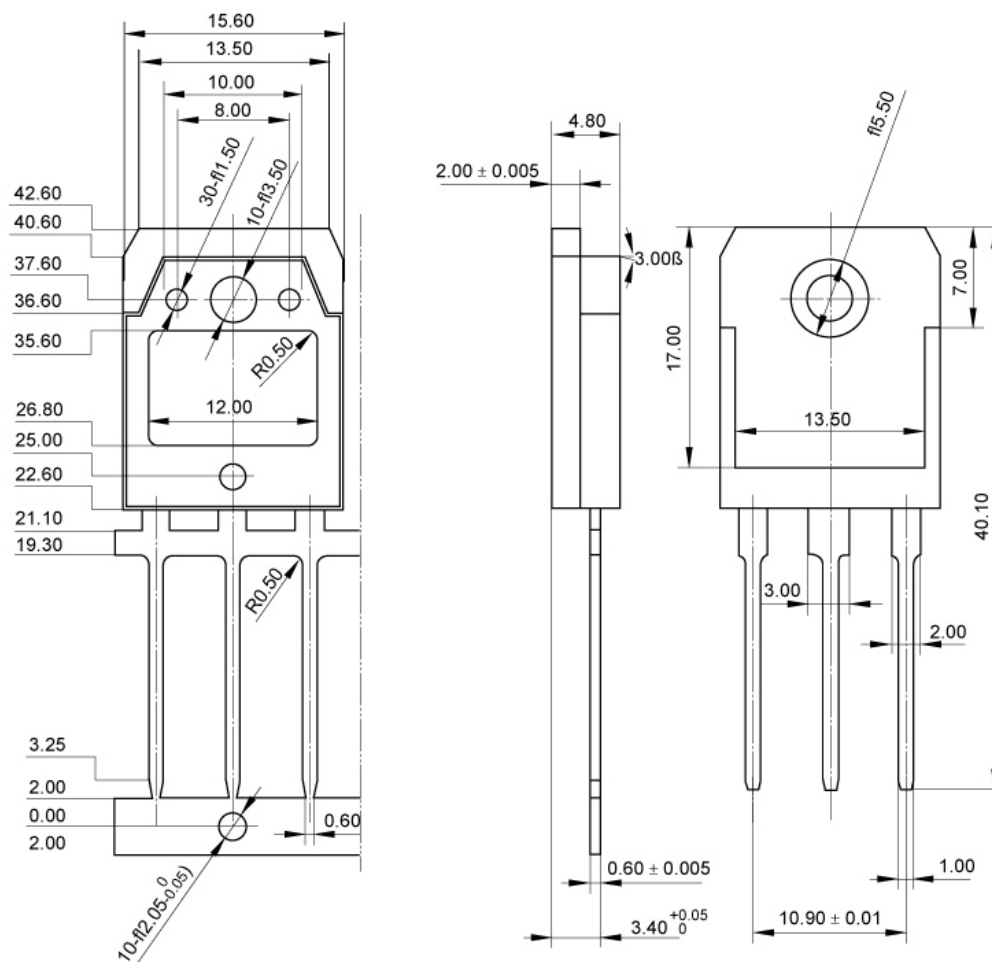


Fig.2 outline dimensions (unindicated tolerance: ±0.10 mm)